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Key Features of Renesas Electronics' New Power MOSFETs

Product Name	Polarity	Package	Drain to Source Voltage (V)	Drain Current (A)	Total Power Dissipation (TC = 25℃) (W)	Drain to Source On-State Resistance (VGS = 10 V) (mohm)	Total Gate Charge TYP. (nC)
NP35N04YUK *	Nch	HSON	40	35	97	5.5	38
NP35N055YUK *	Nch	HSON	55	35	97	7.0	38
NP60N04MUK *	Nch	TO-220	40	60	105	5.0	42
NP60N04NUK *	Nch	TO-262	40	60	105	5.0	42
NP60N04VUK *	Nch	TO-252	40	60	105	4.6	42
NP60N055MUK *	Nch	TO-220	55	60	105	6.7	42
NP60N055NUK *	Nch	TO-262	55	60	105	6.7	42
NP60N055VUK *	Nch	TO-252	55	60	105	6.3	42
NP75N04YUK *	Nch	HSON	40	75	138	3.3	61
NP75N055YUK *	Nch	HSON	55	75	138	5.3	61
NP89N04MUK *	Nch	TO-220	40	90	147	3.25	68
NP89N04NUK *	Nch	TO-262	40	90	147	3.25	68
NP89N04PUK *	Nch	TO-263	40	90	147	2.8	68
NP89N055MUK *	Nch	TO-220	55	90	147	4.35	68
NP89N055NUK *	Nch	TO-262	55	90	147	4.35	68
NP89N055PUK *	Nch	TO-263	55	90	147	3.95	68
NP90N04VUK *	Nch	TO-252	40	90	147	3.0	68
NP90N055VUK *	Nch	TO-252	55	90	147	4.1	68
NP90N04MUK *	Nch	TO-220	40	90	176	2.95	84
NP90N04NUK *	Nch	TO-262	40	90	176	2.95	84
NP90N055MUK *	Nch	TO-220	55	90	176	3.85	84
NP90N055NUK *	Nch	TO-262	55	90	176	3.85	84
NP100N04PUK *	Nch	TO-263	40	100	176	2.3	84

Product Name	Polarity	Package	Drain to Source Voltage (V)	Drain Current (A)	Total Power Dissipation (TC = 25℃) (W)	Drain to Source On-State Resistance (VGS = 10 V) (mohm)	Total Gate Charge TYP. (nC)
NP100N055PUK *	Nch	TO-263	55	100	176	3.2	84
NP109N04PUK *	Nch	TO-263	40	110	250	1.75	130
NP109N055PUK *	Nch	TO-263	55	110	250	2.3	130
NP110N04PUK *	Nch	TO-263	40	110	348	1.4	200
NP110N055PUK *	Nch	TO-263	55	110	348	1.75	200
NP160N04TUK *	Nch	TO-263-7p	40	160	250	1.5	130
NP160N055TUK *	Nch	TO-263-7p	55	160	250	2.1	130
NP180N04TUK *	Nch	TO-263-7p	40	180	348	1.05	200
NP180N055TUK *	Nch	TO-263-7p	55	180	348	1.4	200

* Under development